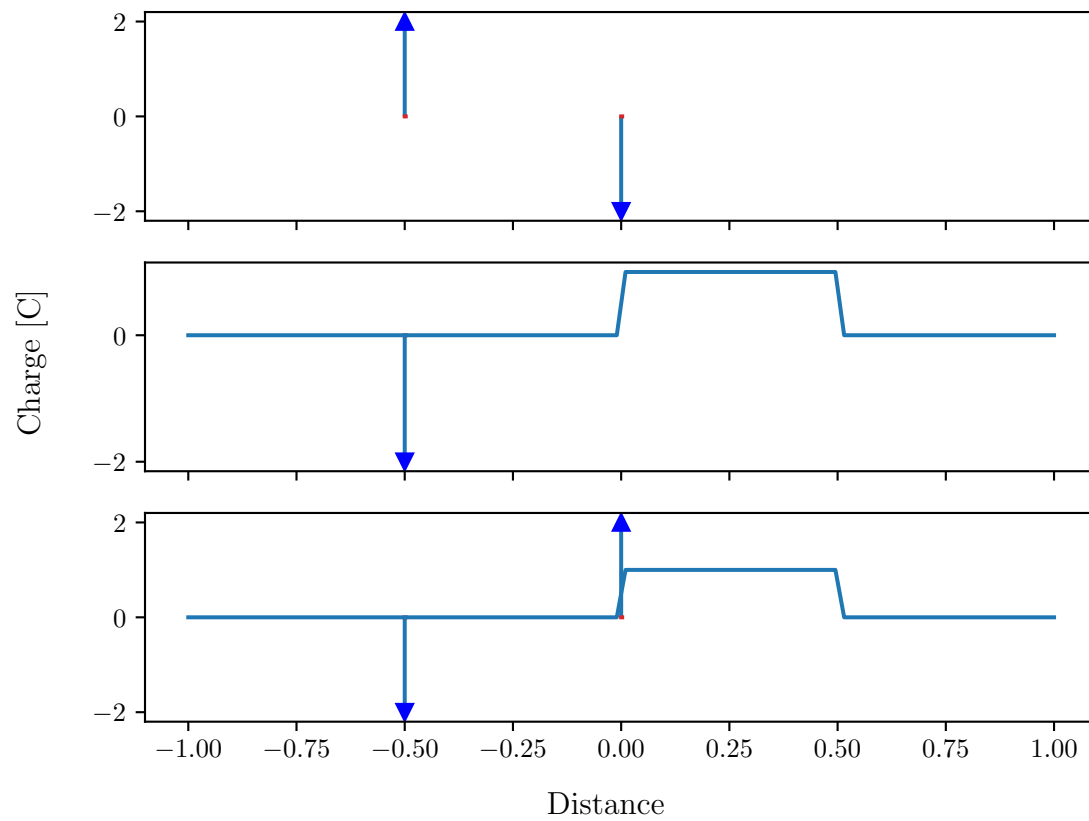
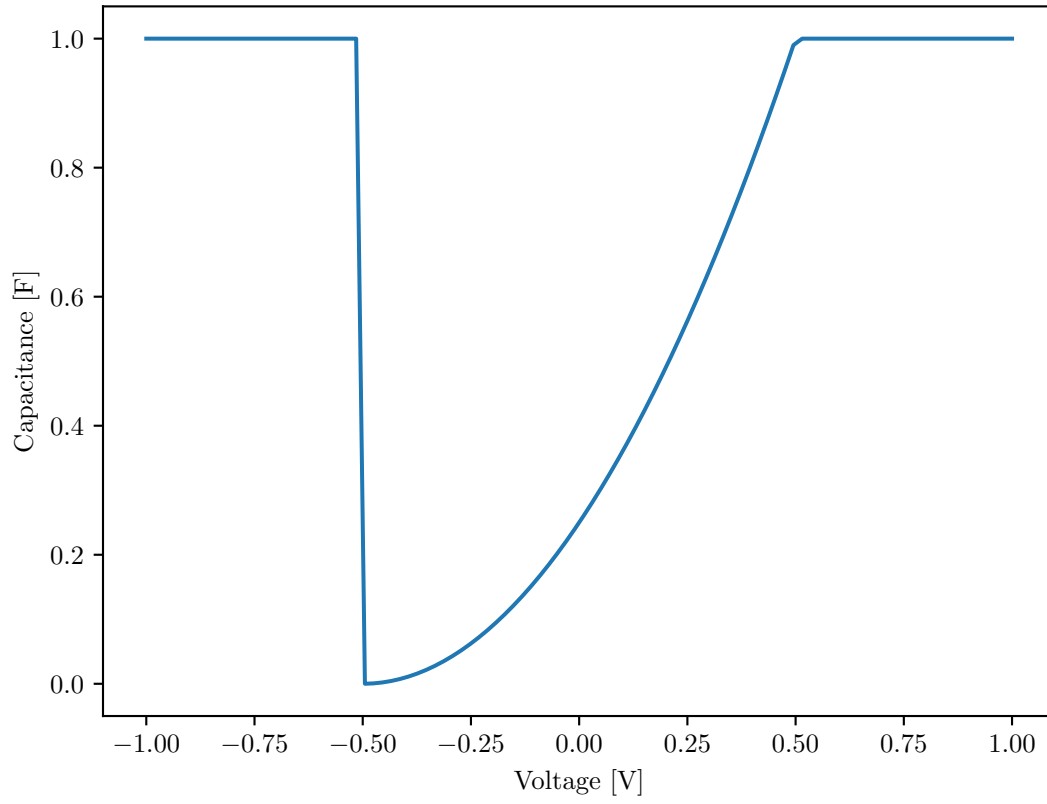


EE 105 HW 08**1**



2

$$T = 300 \text{ K} \quad (1)$$

$$\phi_M = 4.5 \text{ eV} \quad (2)$$

$$\epsilon_{\text{Si}} = 11.7\epsilon_0 \quad (3)$$

$$\chi = 4.05 \text{ eV} \quad (4)$$

$$E_g = 1.12 \text{ eV} \quad (5)$$

$$n_i = 1 \times 10^{10} \text{ cm}^{-3} \quad (6)$$

$$N_a = 1 \times 10^{16} \text{ cm}^{-3} \quad (7)$$

$$\epsilon_{\text{ox}} = 3.9\epsilon_0 \quad (8)$$

$$t_{\text{ox}} = 5 \text{ nm} \quad (9)$$

$$(10)$$

(a)

$$\phi_{\text{Si}} = \chi + \frac{kT}{q} \ln \left(\frac{N_a}{n_i} \right) + \frac{E_g}{2} = 4.967 \text{ eV} \quad (11)$$

$$V_{fb} = \frac{\phi_M - \phi_{\text{Si}}}{q} = -0.467 \text{ V} \quad (12)$$

(b)

$$V_t = V_{fb} + \gamma \sqrt{2|\phi_p|} - 2|\phi_p| \quad (13)$$

$$= V_{fb} + \frac{t_{ox}}{\epsilon_{ox}} \sqrt{2\epsilon_s q N_a} \sqrt{2 \frac{kT}{q} \ln \left(\frac{N_a}{N_i} \right)} + 2 \frac{kT}{q} \ln \left(\frac{N_a}{N_i} \right) \quad (14)$$

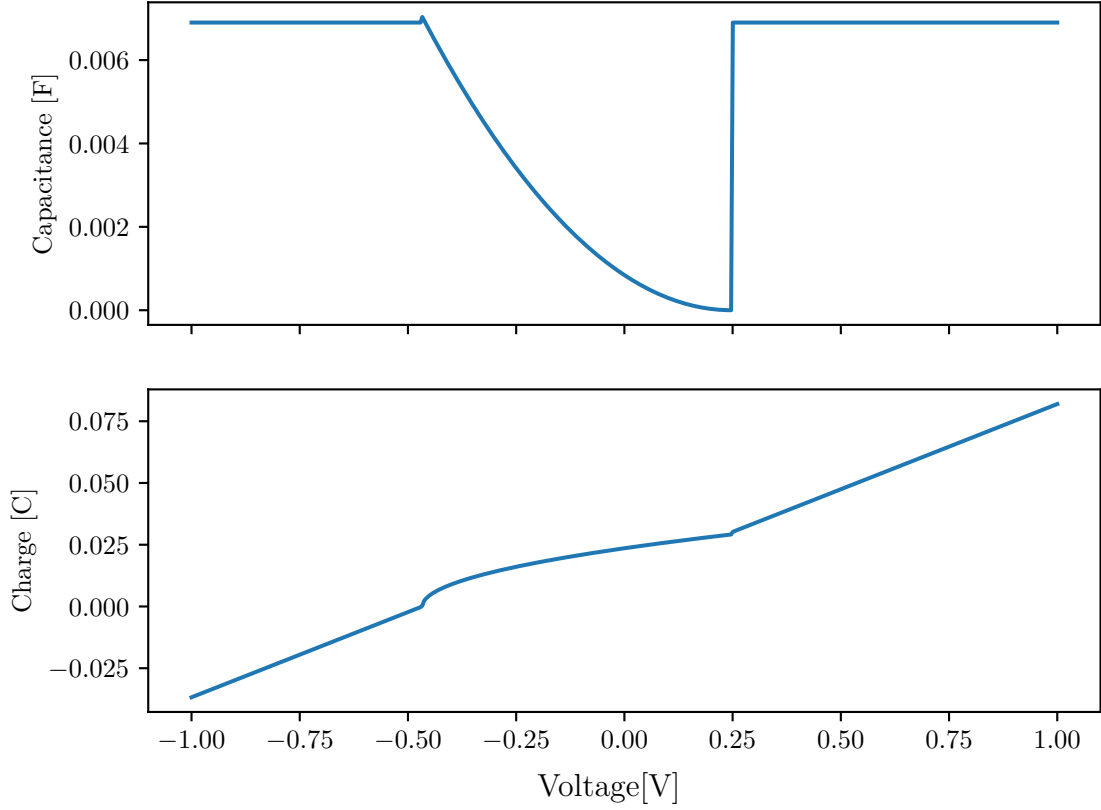
$$= 0.318 \text{ V} \quad (15)$$

(c)

$$C_{acc} = C_{ox} = \frac{\epsilon_{ox}}{t_{ox}} = 6.91 \text{ mF m}^{-2} \quad (16)$$

(d)

$$C_{inv} = C_{ox} = \frac{\epsilon_{ox}}{t_{ox}} = 6.91 \text{ mF m}^{-2} \quad (17)$$



(e)

3

$$W = 50 \mu\text{m} \quad (18)$$

$$L = 1 \mu\text{m} \quad (19)$$

$$T_{\text{ox}} = 10 \text{ nm} \quad (20)$$

$$\epsilon_{\text{ox}} = 4\epsilon_0 \quad (21)$$

$$\epsilon_{\text{Si}} = 12\epsilon_0 \quad (22)$$

$$N_a = 1 \times 10^{15} \text{ cm}^{-3} \quad (23)$$

$$n_i = 1 \times 10^{10} \text{ cm}^{-3} \quad (24)$$

$$V_{fb} = 0 \text{ V} \quad (25)$$

$$\mu_n = 800 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1} = 0.08 \text{ m}^2 \text{ V}^{-1} \text{ s}^{-1} \quad (26)$$

$$T = 300 \text{ K} \quad (27)$$

(a)

$$V_T = \frac{T_{\text{ox}}}{\epsilon_{\text{ox}}} \sqrt{2\epsilon_s q N_a} \sqrt{2 \frac{kT}{q} \ln \left(\frac{N_a}{N_i} \right)} + 2 \frac{kT}{q} \ln \left(\frac{N_a}{N_i} \right) = 0.635 \text{ V} \quad (28)$$

(b) Since $V_{GS} > V_T$ and $V_{DS} < V_{GS} - V_T$, the MOSFET is in linear/triode mode,

$$I_{DS} = \frac{W}{L} \mu_n C_{ox} \left(V_{GS} - V_T - \frac{V_{DS}}{2} \right) = 12.25 \text{ mA} \quad (29)$$

(c)

$$Q_{N,S} = C_{\text{ox}} (V_{GS} - V_T - \cancel{V(0)})^0 = 4.83 \text{ mC m}^{-2} \quad (30)$$

$$Q_{N,D} = C_{\text{ox}} (V_{GS} - V_T - \cancel{V(0)})^{V_{DS}} = 1.29 \text{ mC m}^{-2} \quad (31)$$

$$(32)$$

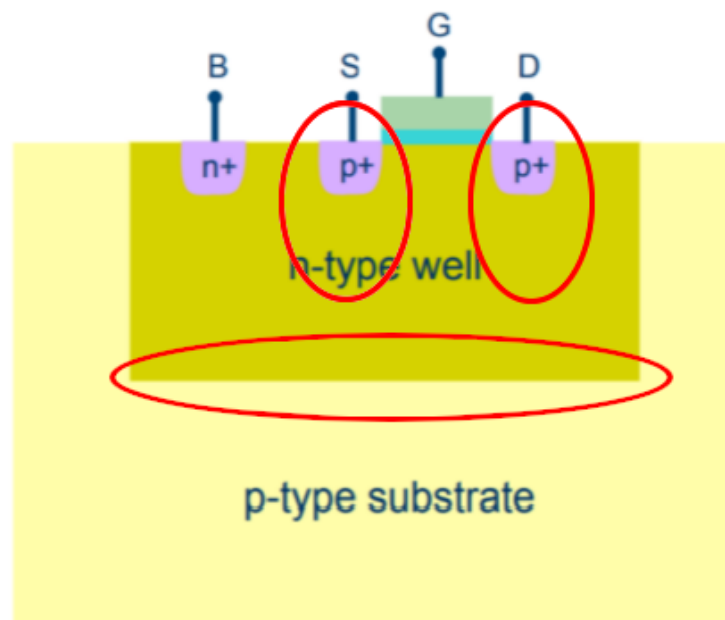
(d) Since $V_{GS} > V_T$ and $V_{DS} > V_{GS} - V_T$, the MOSFET is in saturation mode,

$$I_{DS} = \frac{W}{L} \frac{\mu_n C_{ox}}{2} (V_{GS} - V_T)^2 (1 + \cancel{AV_{DS}})^0 = 13.19 \text{ mA} \quad (33)$$

4

Transistor	Mode
i	Linear/Triode
ii	Saturation
iii	Linear/Triode
iv	Linear/Triode
v	Saturation
vi	Cutoff

(a)



(b)